

Amendments to the Specification

At page 1 before the "Technical Field" section, please insert the following:

--RELATED PATENT DATA

This patent resulted from a divisional application of U.S. Patent Application Serial No. 10/094,580, filed March 6, 2002, entitled "Plasma Enhanced Chemical Vapor Deposition Method of Forming Titanium Silicide Comprising Layers", naming Cem Basceri, Irina Vasilyeva, Ammar Derraa, Philip H. Campbell and Gurtej S. Sandhu as inventors, the disclosure of which is incorporated by reference.—

Please amend the paragraph beginning at line 13 on page 7 to read as follows:

In accordance with an aspect of the invention, a substrate is positioned within a chemical vapor deposition reactor. By way of example only, the ~~first~~ substrate typically will comprise a semiconductor wafer or other substrate. In the context of this document, the term "semiconductor substrate" or "semiconductive substrate" is defined to mean any construction comprising semiconductive material, including, but not limited to, bulk semiconductive materials such as a semiconductive wafer (either alone or in assemblies comprising other materials thereon), and semiconductive material layers (either alone or in assemblies comprising other materials). The term "substrate" refers to any supporting structure, including, but not limited to, the semiconductive substrates described above.

Please amend the paragraph beginning at line 1 on page 10 to read as follows:

Regardless of whether any silane is fed during the first feeding, after the first feeding, TiCl_4 and at least one silane are fed to the chamber for a second period of time effective to plasma enhance chemical vapor deposit a titanium silicide comprising layer on the substrate. Plasma generation can be direct within the chamber, or remote therefrom. Any suitable gas components within the chamber, whether existing or yet-to-be developed, including TiCl_4 and a silane ~~is~~ are contemplated. As above, an exemplary silane is SiH_4 , with silanes including more than one silicon atom, and organic silanes, also of course being contemplated. By way of example only, one preferred process of forming a titanium silicide comprising layer includes plasma enhanced chemical vapor depositions at an exemplary power range of from 200 watts to 600 watts, a substrate temperature range of from 600°C to 700°C and a chamber pressure range of from 3 Torr to 6 Torr. Exemplary processing gases include SiH_4 at from 0.5 sccm to 10 sccm, TiCl_4 at from 50 sccm

to 150 sccm, Ar at from 2,000 sccm to 6,000 sccm, He at from 1,000 sccm to 2,000 sccm and H₂ at from 200 sccm to 10,000 sccm in a 6.55 liter chamber. Such exemplary processing can be conducted to plasma enhance chemical vapor deposit a titanium silicide comprising layer which consists essentially of titanium silicide. The second period of time for the deposition is advantageously chosen to provide the selected thickness deposition of a desired titanium silicide comprising layer over the substrate.